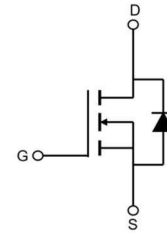


APG055N12T

N-Channel Enhancement Mosfet

Features

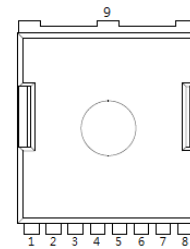
- 120V,200A
 $R_{DS(on)} < 5.5m\Omega @ V_{GS}=10V$ TYP:5.0m Ω
 $R_{DS(on)} < 7.5m\Omega @ V_{GS}=6V$ TYP:6.5m Ω
- Advanced trench cell design
- Low Thermal Resistance
- MSL1



Schematic Diagram

Applications

- Motor drivers
- DC - DC Converter



TOLL-8L

1	Gate(G)
2,3,4,5,6,7,8	Source(S)
9	Drain(D)

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G055N12T	APG055N12T	TOLL-8L	-	-	2000

ABSOLUTE MAXIMUM RATINGS ($T_J=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_C = 25^{\circ}C$)	I_D	200	A
Continuous Drain Current ($T_C = 100^{\circ}C$)	I_D	143	A
Pulsed Drain Current ^(1,2,3)	I_{DM}	396	A
Single Pulsed Avalanche Energy ⁽¹⁾	E_{AS}	922	mJ
Power Dissipation	P_D	156	W
Thermal Resistance from Junction to Case ⁽¹⁾	$R_{\theta JC}$	3.5	$^{\circ}C/W$
Thermal Resistance- Junction to Ambient	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MOSFET ELECTRICAL CHARACTERISTICS(T_J=25°C unless otherwise noted)

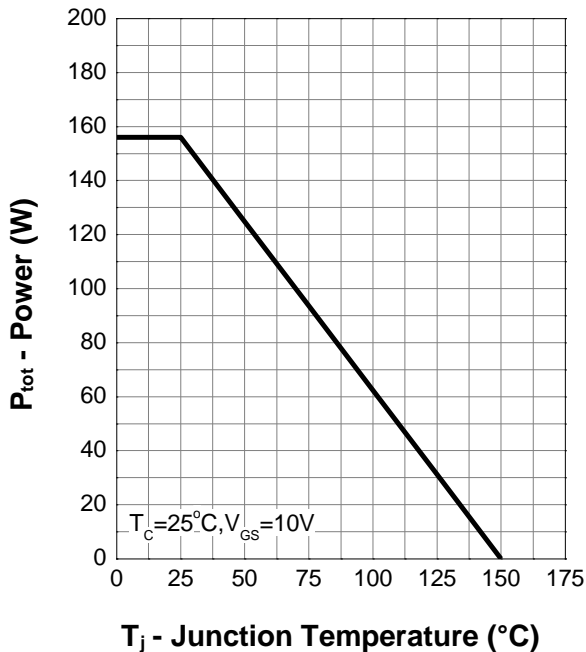
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	120	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =96V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	-	4.0	V
Drain-source on-resistance ⁽²⁾	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	5.0	5.5	mΩ
		V _{GS} =6V, I _D =10A		6.5	7.5	mΩ
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =60V, V _{GS} =0V, f =1.0MHz	-	4779	-	pF
Output Capacitance	C _{oss}		-	570	-	
Reverse Transfer Capacitance	C _{rss}		-	34	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} =60V, I _D =50A, R _G =3.9Ω, , R _L = 3 Ω, I _{DS} = 20 A	-	16	-	ns
Turn-on rise time	t _r		-	27	-	
Turn-off delay time	t _{d(off)}		-	51	-	
Turn-off fall time	t _f		-	27	-	
Total Gate Charge	Q _g	V _{DS} =60V, I _D =20A, V _{GS} =10V	-	80	-	nC
Gate-Source Charge	Q _{gs}		-	24	-	
Gate-Drain Charge	Q _{gd}		-	18	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽²⁾	V _{SD}	T _J =25°C, V _{GS} =0V, I _S =20A	-	-	1.3	V
Diode Forward current	I _S	T _C =25°C	-	-	200	A
Body Diode Reverse Recovery Time	t _{rr}	T _J =25°C, I _F =20A, di/dt=100A/us		92		ns
Body Diode Reverse Recovery Charge	Q _{rr}	T _J =25°C, I _F =20A, di/dt=100A/us		337		uc

Notes:

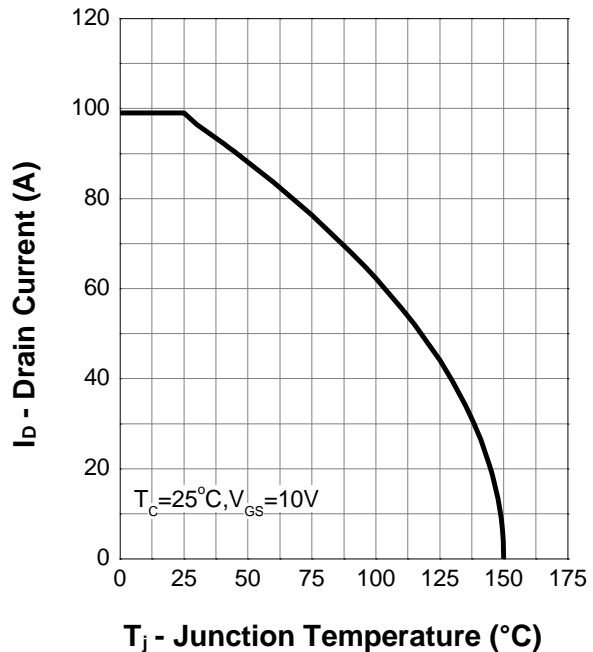
1. Surface Mounted on 1 in² pad area, t ≤ 10 sec
2. Pulse width ≤ 300 μs, duty cycle ≤ 2 %
3. Thermal resistance, junction - case, bottom with thermal pad

Typical Characteristics (Cont.)

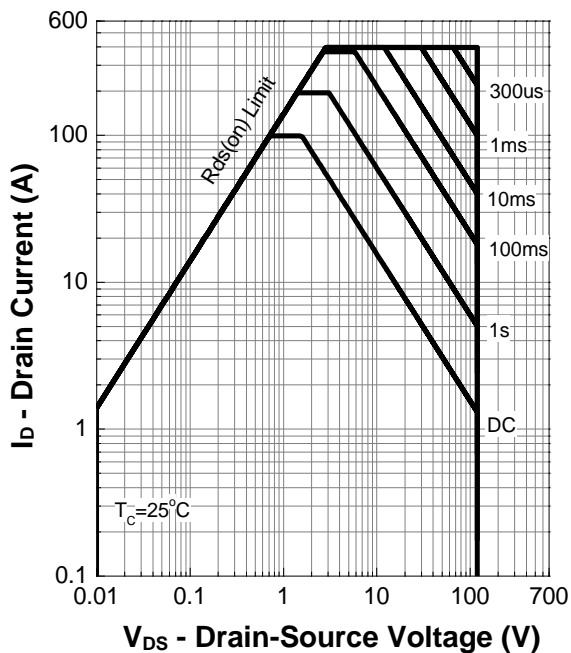
Power Capability



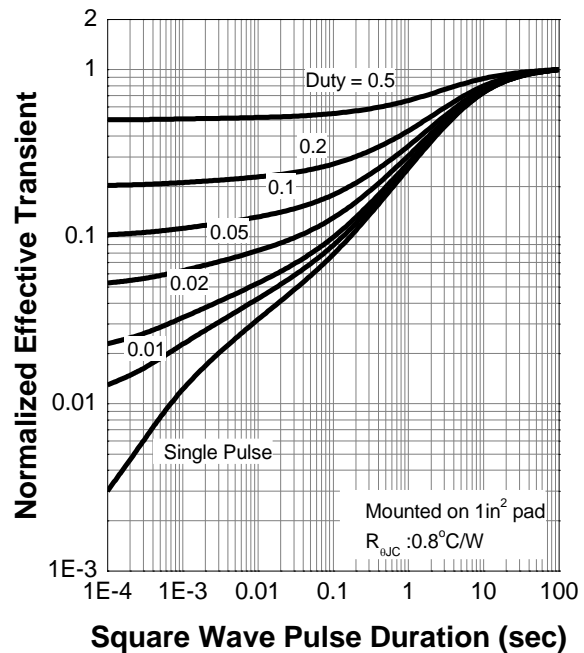
Current Capability



Safe Operation Area

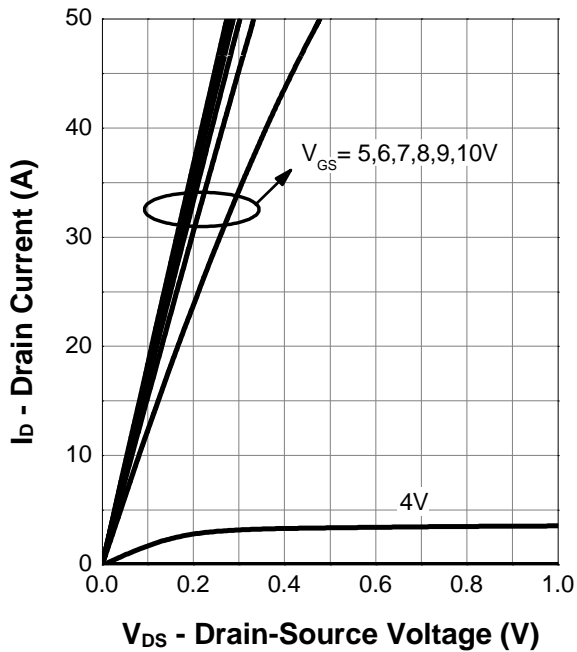


Transient Thermal Impedance

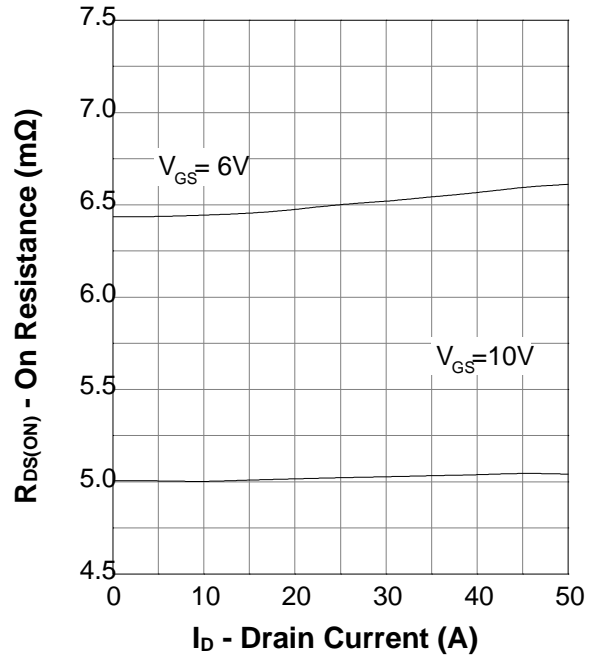


Typical Characteristics (Cont.)

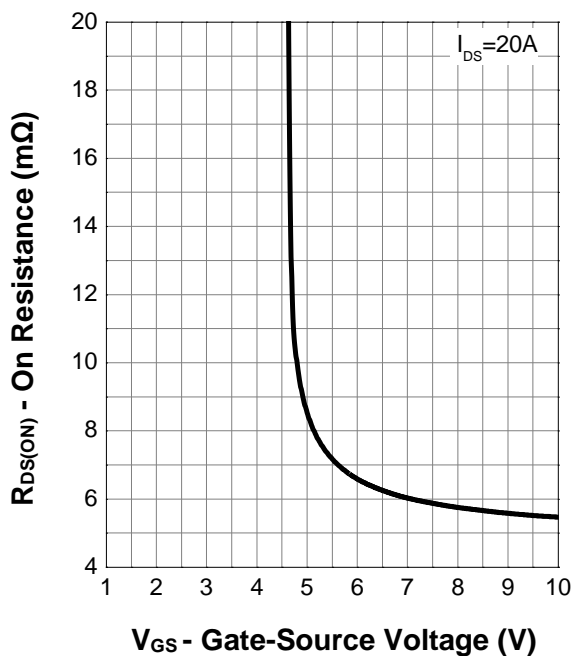
Output Characteristics



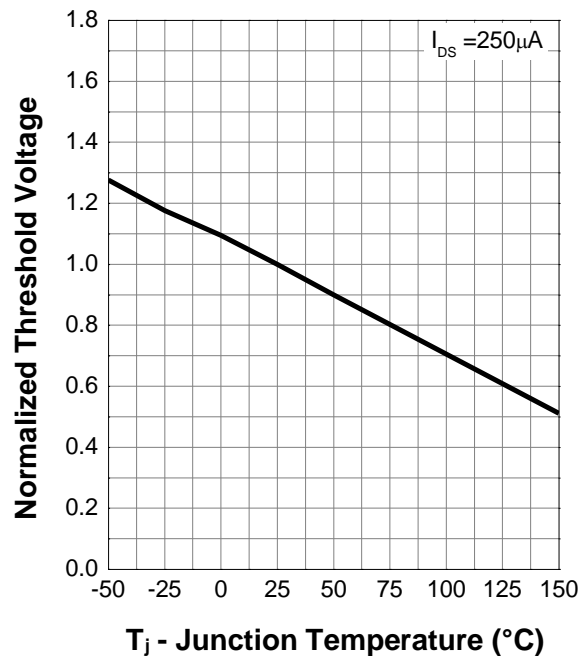
On Resistance



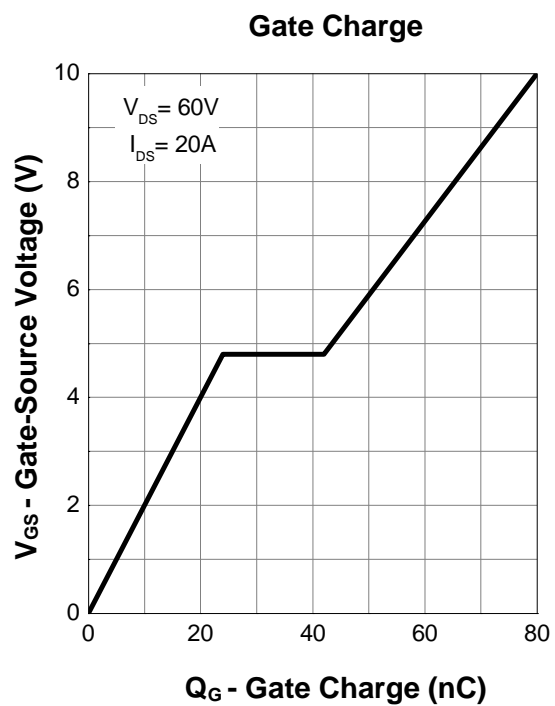
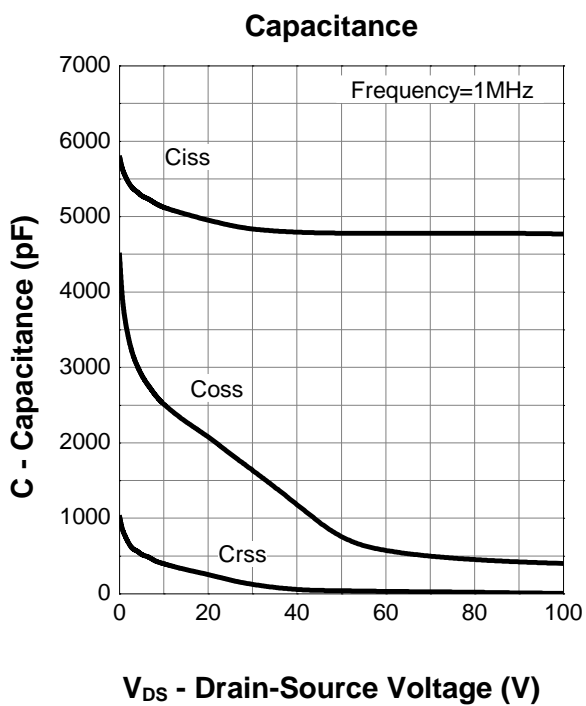
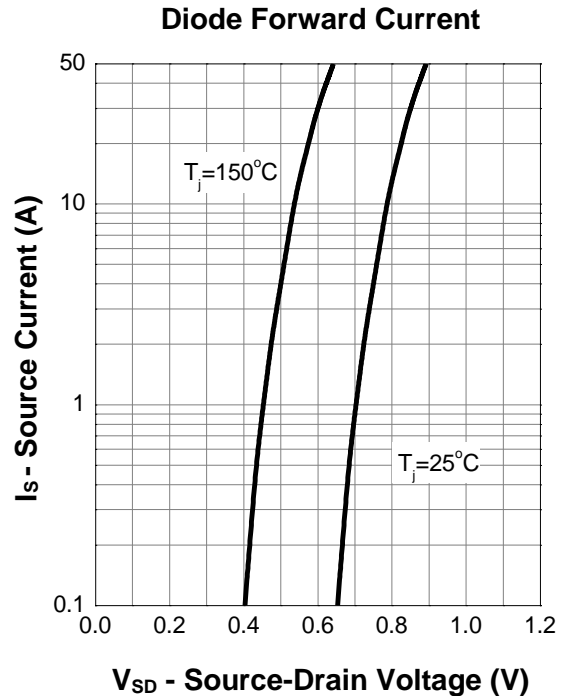
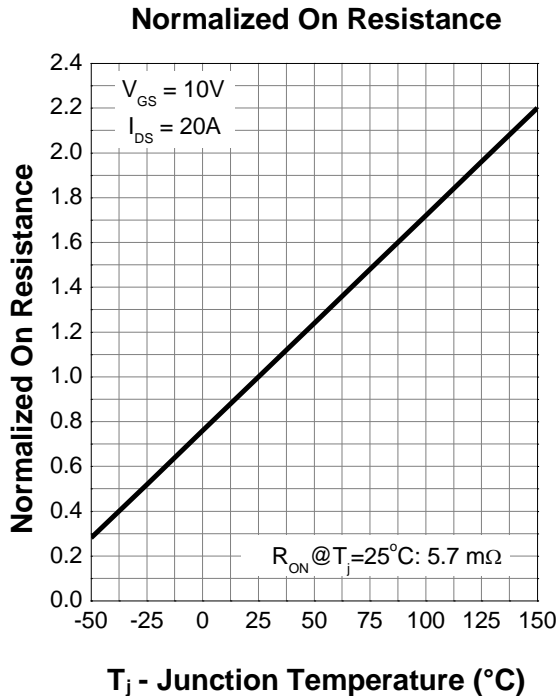
Transfer Characteristics



Normalized Threshold Voltage

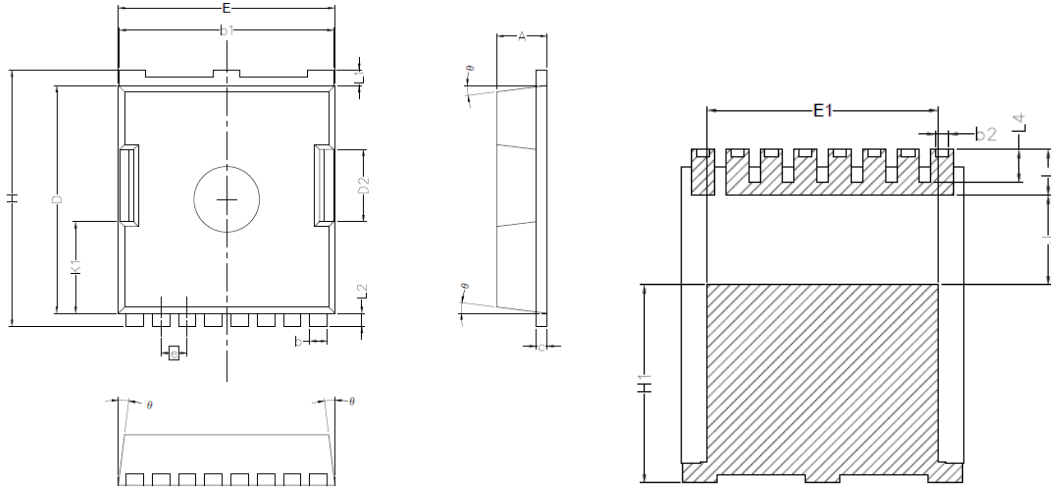


Typical Characteristics (Cont.)



Package Dimensions

TOLL-8L



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	2.20	2.40
b	0.90	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°

Revision History

Revision	Release	Remark
V1.0	2023/03/07	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Allpower assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements, the information described or contained herein may be changed without prior notice.